

# DC – 16 GHz GaAs HBT MMIC Divide-by-8 Prescaler

# **Technical Data**

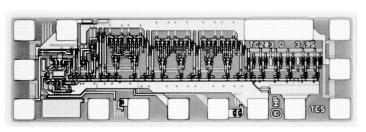
### HMMC-3008

### **Features**

- Wide Frequency Range: 0.2 - 16 GHz
- High Input Power Sensitivity: On-chip pre- and post-amps -20 to +10 dBm (1 - 10 GHz) -15 to +10 dBm (10 - 12 GHz) -10 to +5 dBm (12 - 15 GHz)
- **Dual-mode P<sub>out</sub>: (Chip Form)** 0 dBm [0.5 V<sub>p-p</sub>] @ 66 mA +6.0 dBm [0.99 V<sub>p-p</sub>] @ 86 mA
- Low Phase Noise: -153 dBc/Hz @ 100 kHz Offset
- (+) or (-) Single Supply Bias Operation
- Wide Bias Supply Range: 4.5 to 6.5 volt operating range
- Differential I/0 with on-chip 50 Ω matching

# **Description**

The HMMC-3008 GaAs HBT MMIC Prescaler offers DC to 16 GHz frequency translation for use in communications and EW systems incorporating highfrequency PLL oscillator circuits and signal-path down conversion applications. The prescaler provides a large input power sensitivity window and low phase noise. In addition to the features listed above the device offers input disable and circuit powerdown contact pads to eliminate any self-oscillation condition or reduced power consumption.



Chip Size: Chip Size Tolerance: Chip Thickness: Pad Dimensions: 1330 x 440  $\mu$ m (52.4 x 17.3 mils) ±10  $\mu$ m (±0.4 mils) 127 ± 15  $\mu$ m (5.0 ± 0.6 mils) 70 x 70  $\mu$ m (2.8 x 2.8 mils)

#### Absolute Maximum Ratings<sup>[1]</sup>

Symbol	<b>Parameters/Conditions</b>	Units	Min.	Max.
V <sub>CC</sub>	Bias Supply Voltage	volts		+7
V <sub>EE</sub>	Bias Supply Voltage	volts	-7	
$ V_{CC} - V_{EE} $	Bias Supply Delta	volts	+7	
V <sub>Disable</sub>	Pre-amp Disable Voltage	volts	V <sub>EE</sub>	V <sub>CC</sub>
V <sub>PwrDwn</sub>	Prescaler Power-Down Voltage	volts	V <sub>EE</sub>	V <sub>CC</sub>
V <sub>Logic</sub>	Logic Threshold Voltage	volts	V <sub>CC</sub> -1.5	V <sub>CC</sub> -1.2
P <sub>in(CW)</sub>	CW RF Input Power	dBm		+10
V <sub>RFin</sub>	DC Input Voltage (@ RFin or RFin Ports)	volts		$V_{CC} \pm 0.5$
T <sub>BS</sub> <sup>[2]</sup>	Backside Operating Temp	°C	-40	+85
T <sub>STG</sub>	Storage Temperature	°C	-65	+165
T <sub>max</sub>	Maximum Assembly Temp (60 seconds max.)	°C		310

Notes:

- 1. Operation in excess of any parameter limit (except  $T_{BS})$  may cause permanent damage to the device.
- 2.  $MTTF > 1 \times 10^6$  hours @  $T_{BS} < 85^{\circ}C$ . Operation in excess of maximum operating temperature ( $T_{BS}$ ) will degrade MTTF.

Symbol	Parameters and Test Conditions	Units	Min.	Typ.	Max.
V <sub>CC</sub> - V <sub>EE</sub>	Operating Bias Supply Difference <sup>[1]</sup>	volts	4.5	5.0	6.5
I or I	Bias Supply Current ( <b>HIGH</b> Output Power Configuration <sup>[2]</sup> : $V_{PwrSel} = V_{EE}$ )	mA	63	86	99
$ I_{CC} $ or $ I_{EE} $	Bias Supply Current (LOW Output Power Configuration <sup>[2]</sup> : V <sub>PwrSel</sub> = open)	mA	56	66	76
$V_{RFin(q)} \ V_{RFout (q)}$	Quiescent DC Voltage appearing at all RF Ports	volts		V <sub>CC</sub>	
V <sub>Logic</sub>	Nominal ECL Logic Level (V <sub>Logic</sub> contact self-bias voltage, generated on-chip)	volts	V <sub>CC</sub> - 1.45	V <sub>CC</sub> - 1.35	V <sub>CC</sub> - 1.25
I <sub>EE(off)</sub>	Residual Bias Supply Current ( $V_{PwrDwn} = V_{CC}$ )	mA		6	

**DC Specifications/Physical Properties**<sup>[1]</sup>, ( $T_A = 25^{\circ}C$ ,  $V_{CC} - V_{EE} = 5.0$  V unless otherwise listed)

Notes:

1. Prescaler will operate over full specified supply voltage range.  $V_{CC}$  or  $V_{EE}$  not to exceed limits specified in Absolute Maximum Ratings section.

2. High output power configuration:  $P_{out} = +6.0 \text{ dBm} [V_{out} = 0.99 V_{p-p}]$ , Low output power configuration:  $P_{out} = 0 \text{ dBm} [V_{out} = 0.5 V_{p-p}]$ .

Symbol	Parameters and Test Conditions		Min.	Тур.	Max.
f <sub>in(max)</sub>	Maximum input frequency of operation	GHz	16	18	
$f_{in(min)}$				0.2	0.5
fSelf-Osc.	Output Self-Oscillation Frequency <sup>[2]</sup>	GHz		1.7	
	@ DC, (Square-wave input)	dBm	-15	>-25	+10
	@ $f_{in} = 500$ MHz, (Sine-wave input)	dBm	-15	>20	+10
P <sub>in</sub>	$f_{\rm in} = 1$ to 10 GHz	dBm	-15	>-25	+10
	$f_{\rm in} = 10$ to 12 GHz	dBm	-10	>-15	+10
	$f_{\rm in} = 12$ to 15 GHz	dBm	-4	>-10	+4
RL	Small-Signal Input/Output Return Loss (@ $f_{in}$ < 12 GHz)	dB		15	
S <sub>12</sub>	nall-Signal Reverse Isolation (@ $f_{in} < 12$ GHz) dB			30	
$\phi_{N}$	SSB Phase Noise (@ $P_{in} = 0$ dBm, 100 kHz offsetdBc/Hzfrom a $f_{out} = 1.2$ GHz CarrierdBc/Hz		-153		
Jitter	Input Signal Time Variation @ Zero-Crossing $(f_{in} = 10 \text{ GHz}, P_{in} = -10 \text{ dBm})$	ps		1	
T <sub>r</sub> or T <sub>f</sub>	Output Edge Speed (10% to 90% rise/fall time)	ps		70	

# **HMMC-3008 (÷8) RF Specifications,** $(T_A = 25^{\circ}C, Z_O = 50\Omega, V_{CC} - V_{EE} = 5.0 \text{ V})$

Notes:

<sup>1.</sup> For sine-wave input signal. Prescaler will operate down to D.C. for square-wave input signal. Minimum divide frequency limited by input slew-rate.

<sup>2.</sup> Prescaler may exhibit this output signal under bias in the absence of an RF input signal. This condition may be eliminated by use of the Pre-amp Disable (V<sub>Disable</sub>) or Prescaler Power-Down (V<sub>PwrDwn</sub>) features, or the Differential Input de-biasing technique.

Symbol	Parameters and Test Conditions	Units	Min.	Тур.	Max.
	@ $f_{out} < 1 \text{ GHz}$	dBm	4.0	6.0	
Pout	@ $f_{out} = 1.25 \text{ GHz}$	dBm	4.0	6.0	
	@ $f_{out} = 1.5 \text{ GHz}$	dBm	3.7	5.7	
	@ f <sub>out</sub> < 1 GHz	volts	0.79	0.99	
V <sub>out(p-p)</sub>	@ $f_{out} = 1.25 \text{ GHz}$	volts	0.79	0.99	
· ····································	@ $f_{out} = 1.5 \text{ GHz}$	volts	0.76	0.96	
P <sub>Spitback</sub>	$f_{out}$ power level appearing at RFin or $\overline{RFin}$ (@ $f_{in} = 12$ GHz, Unused RFout or $\overline{RFout}$ unterminated)	dBm		-55	
<sup>1</sup> Spitback	$f_{out}$ power level appearing at RFin or RFin (@ $f_{in} = 12$ GHz, Both RFout & RFout <b>terminated</b> )	dBm		-75	
P <sub>feedthru</sub>	Power level of $f_{in}$ appearing at RFout or RFout (@ $f_{in} = 12$ GHz, $P_{in} = 0$ dBm, Referred to $P_{in} (f_{in})$ )	dBc		-30	
H <sub>2</sub>	Second harmonic distortion output level (@ $f_{out} = 1.5$ GHz, Referred to $P_{out} (f_{out})$ )	dBc		-30	

**HMMC-3008 RF Specifications, High Output Power Operating Mode**<sup>[1]</sup> ( $T_A = 25^{\circ}C, Z_O = 50\Omega, V_{CC} - V_{EE} = 5.0 V$ )

# Low Output Power Operating Mode<sup>[2]</sup>

Symbol	Parameters and Test Conditions	Units	Min.	Тур.	Max.
	@ f <sub>out</sub> < 1 GHz	dBm	-2	0	
Pout	@ $f_{out} = 1.25 \text{ GHz}$	dBm	-2	0	
	@ $f_{out} = 1.5 \text{ GHz}$	dBm	-2.3	-0.3	
	@ $f_{out} < 1 \text{ GHz}$	volts	0.39	0.5	
V <sub>out(p-p)</sub>	@ $f_{out} = 1.25 \text{ GHz}$	volts	0.39	0.5	
i and the	@ $f_{out} = 1.5 \text{ GHz}$	volts	0.38	0.48	
Paul	$f_{out}$ power level appearing at RFin or RFin (@ $f_{in} = 12$ GHz, Unused RFout or RFout <b>unterminated</b> )	dBm		-65	
P <sub>Spitback</sub>	$f_{out}$ power level appearing at RFin or RFin (@ $f_{in} = 12$ GHz, Both RFout & RFout <b>terminated</b> )	dBm		-85	
P <sub>feedthru</sub>	Power level of $f_{in}$ appearing at RFout or RFout (@ $f_{in} = 12$ GHz, $P_{in} = 0$ dBm, Referred to $P_{in} (f_{in})$ )	dBc		-30	
H <sub>2</sub>	Second harmonic distortion output level (@ $f_{out} = 1.5$ GHz, Referred to $P_{out} (f_{out})$ )	dBc		-35	

Notes:

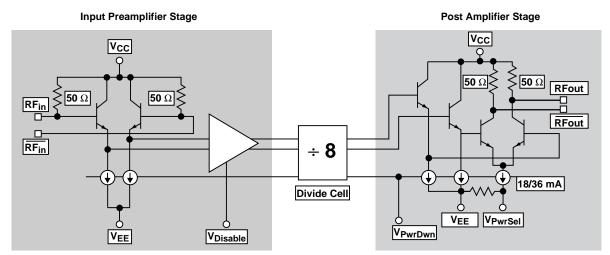


Figure 1. HMMC-3008 Simplified Schematic.

#### **Applications**

The HMMC-3008 is designed for use in high frequency communications, microwave instrumentation and EW radar systems where low phase-noise PLL control circuitry or broad-band frequency translation is required.

# **Operation**

The device is designed to operate when driven with either a singleended or differential sinusoidal input signal over a 200 MHz to 16 GHz bandwidth. Below 200 MHz the prescaler input is "slew-rate" limited requiring fast rising and falling edge speeds to properly divide. The device will operate at frequencies down to DC when driven with a squarewave. AC coupling at the RFin pad is recommended for most applications.

The device can be operated from either a single positive or single negative supply. For positive supply operation  $V_{CC}$  is nominally biased at any voltage in the +4.5 to +6.5 volt range with  $V_{EE}$  (or  $V_{EE}$  &  $V_{PwrSel}$ ) grounded. For negative bias operation  $V_{CC}$  is typically grounded and a negative voltage between -4.5 to -6.5 volts is applied to  $V_{\rm EE}$  (or  $V_{\rm EE}$  &  $V_{\rm PwrSel}$ ).

Several features are designed into this prescaler:

### 1) Dual-Output Power Feature

Bonding both V<sub>EE</sub> and V<sub>PwrSel</sub> pads to either ground (positive bias mode) or the negative supply (negative bias mode), will deliver  $\sim$ 6.0 dBm [0.99 V<sub>p-p</sub>] at the RF output port while drawing ~86 mA supply current. Eliminating the V<sub>PwrSel</sub> connection results in reduced output power and voltage swing, 0 dBm [0.5 V<sub>p-p</sub>] but at a reduced current draw of ~66 mA resulting in less overall power dissipation. (NOTE:  $V_{EE}$ must ALWAYS be bonded and V<sub>PwrSel</sub> must NEVER be biased to any potential other than  $V_{EE}$  or open-circuited.)

# 2) V<sub>Logic</sub> ECL Contact Pad

Under normal conditions no connection or external bias is required to this pad and it is self-biased to the on-chip ECL logic threshold voltage ( $V_{CC}$  -1.35 V). The user can provide an external bias to this pad (1.5 to 1.2 volts

less than  $V_{CC}$ ) to force the prescaler to operate at a system generated logic threshold voltage.

#### 3) Input Disable Feature

By applying an external bias to this contact pad (more positive than  $V_{CC}$  - 1.35 V), the input preamplifier stage is locked into either logic *"high"* or logic *"low"* preventing frequency division and any self-oscillation frequency which may be present.

#### 4) Prescaler Power-Down

By applying an external bias to this contact pad (more positive than  $V_{EE}$  + 3.2V), the supply current can be reduced to ~5 mA also preventing frequency division and any self-oscillation frequency which may be present while decreasing the power dissipation to ~zero.

# 5) Input DC Offset

Another method used to prevent false triggers or self-oscillation conditions is to apply a 20 to 100 mV DC offset voltage between the RFin and RFin ports. This prevents noise or spurious low level signals from triggering the divider.

<b>Optional DC Operating Values/Logic Levels</b> $(T_A = 25^{\circ}C)$	<b>Optional D</b>	<b>C</b> Operating	Values/Logic	Levels (T <sub>A</sub>	$= 25^{\circ}C$
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	1 0 0	-	-		
Function	Symbol	Conditions	Min.	Typical	Max.
			(volts/mA)	(volts/mA)	(volts/mA)
Logic Threshold <sup>[1]</sup>	V <sub>Logic</sub>		V <sub>CC</sub> - 1.5	V <sub>CC</sub> - 1.35	V <sub>CC</sub> - 1.2
	V <sub>Disable(High)</sub> [Disable]		$V_{Logic} + 0.25$	V <sub>Logic</sub>	V <sub>CC</sub>
Input Disable	V <sub>Disable(Low)</sub> [Enable]		V <sub>EE</sub>	V Logic	V <sub>Logic</sub> - 0.25
input Disable	Inc. u	$V_{\rm D} > V_{\rm EE} + 3$	(V <sub>1</sub>	Disable - V <sub>EE</sub> - 3) / 5	500
	I <sub>Disable</sub>	$V_{\rm D} < V_{\rm EE} + 3$		0	
	V <sub>PwrDwn(High)</sub> [Power-Down]		$V_{\rm EE}$ + 3.9	V <sub>EE</sub> + 3.2	V <sub>CC</sub>
Prescaler	V <sub>PwrDwn(Low)</sub> [Power-Up]		V <sub>EE</sub>	v <u>EE</u> + 3.2	$V_{\rm EE}$ + 2.7
Power-Down	Ŧ	$V_{\rm P} > V_{\rm EE} + 2.7$	(V <sub>PwrDwn</sub> -V <sub>EE</sub> - 3) / 500		
	I <sub>PwrDwn</sub>	$V_{\rm P} < V_{\rm EE} + 2.7$		0	

Note:

1. Acceptable voltage range when applied from external source.

#### **Assembly Techniques**

Figure 3 shows the chip assembly diagram for single-ended I/O operation through 16 GHz. For positive supply operation, V<sub>CC</sub> is typically biased to a positive voltage between +4.5 and +6.5 volts and  $V_{EE}$  is grounded. For negative supply operation, V<sub>EE</sub> is typically biased between -4.5 to -6.5 volts and  $V_{CC}$  is grounded. In either case the supply contact to the chip must be capacitively bypassed to provide good input sensitivity and low input power feedthrough. All bonds between the device and this bypass capacitor should be as short as possible to limit the inductance. For operation at frequencies below 1 GHz, a large value capacitor must be added to provide proper RF bypassing.

To aid in providing higher frequency bypassing a special V<sub>CC(Bypass)</sub> pad has been added to the chip and must be tied to RF ground.

In general, AC coupling capacitors are recommended on the RFin and RFout connections to the device. For negative supply operation the AC coupling cap is not critical since V<sub>CC</sub> is typically grounded and the DC voltage present on RFin/RFout is ~0 volts. For positive supply operation, V<sub>CC</sub> is positively biased resulting in a positive DC voltage appearing at RFin or RFout. In this case a AC coupling cap is required.

Due to on-chip 50  $\Omega$  matching resistors at all four RF ports, no external termination is required. However, improved "Spitback" performance (~ 20 dB) and input sensitivity can be achieved by terminating the unused RFout port to  $V_{CC}$  through 50  $\Omega$  (positive supply) or to ground via a 50  $\Omega$ termination (negative supply operation).

For proper handling, die-attach and electrical interconnection techniques of ESD sensitive components see Agilent application note #999, "GaAs MMIC Assembly and Handling Guidelines."

GaAs MMICs are ESD sensitive. Proper precautions should be used when handling these devices.

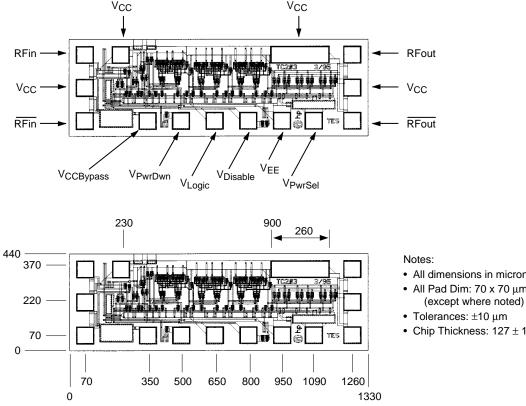


Figure 2. HMMC-3008 Pad Locations and Chip Dimensions.

· All dimensions in microns.

- All Pad Dim: 70 x 70 µm

- Chip Thickness: 127 ± 15 μm

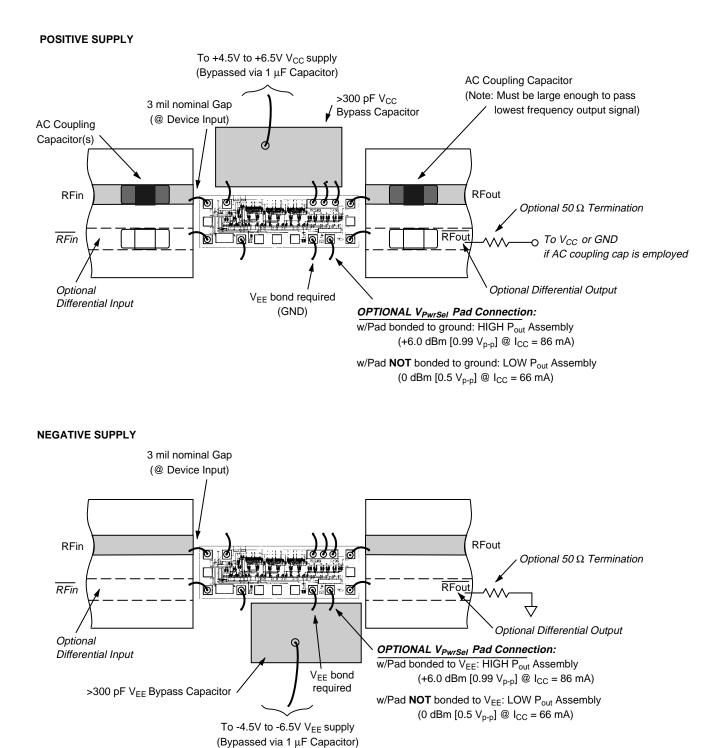


Figure 3. HMMC-3008 Assembly Diagrams.

# **HMMC-3008 Supplemental Data**

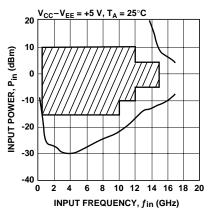


Figure 4. Typical HMMC-3002/3004/3008 Input Sensitivity Window.

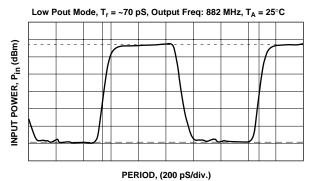
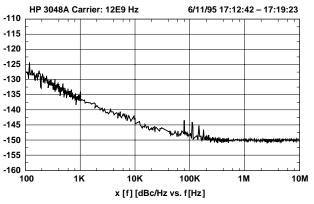


Figure 6. Typical HMMC-3002/3004/3008 Output

Voltage Waveform.







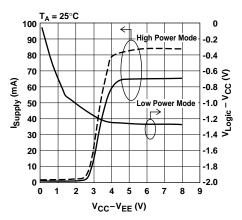


Figure 5. Typical Supply Current & V<sub>Logic</sub> vs. Supply Voltage.

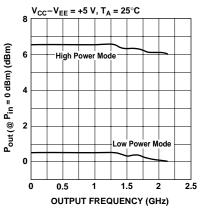


Figure 7. Typical Output Power vs. Output Frequency,  $f_{out}$  (GHz).

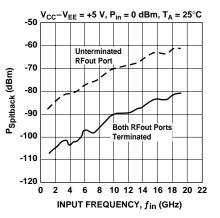
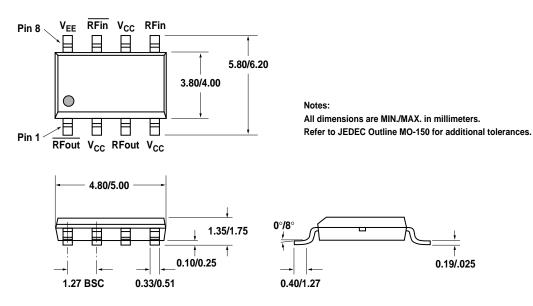
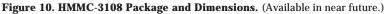
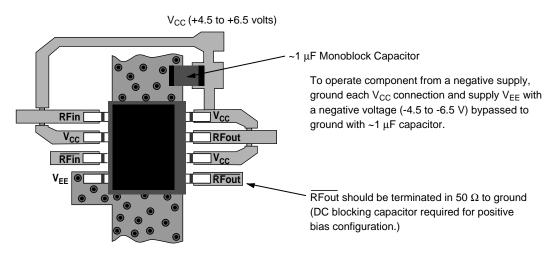


Figure 9. Typical HMMC-3002/3004/3008 *"Spitback"* Power. P(f<sub>out</sub>) appearing at RF input port.









**Figure 11. HMMC-3108 Assembly Diagram.** (Single-supply, positive-bias configuration shown)

This data sheet contains a variety of typical performance data. The information supplied should not be interpreted as a complete list of circuit specifications. In this data sheet the term *typical* refers to the 50th percentile performance. For additional information contact your local Agilent sales representative.

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